

TOSHIBA TRANSISTOR SILICON NPN TRIPLE DIFFUSED TYPE

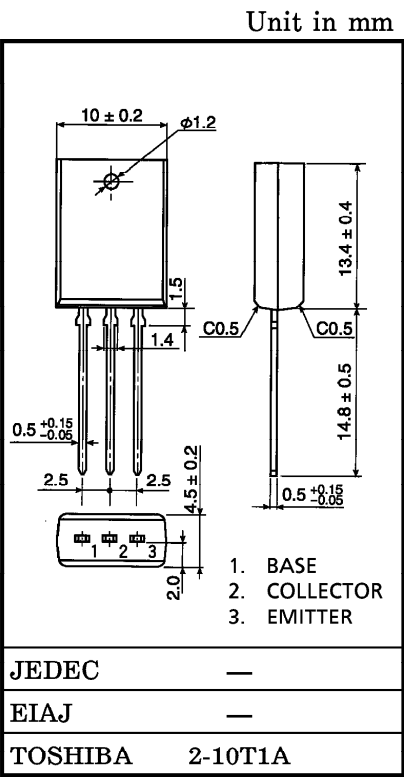
2SD2526

HIGH POWER SWITCHING APPLICATIONS
HAMMER DRIVE, PULSE MOTOR DRIVE APPLICATIONS

- High DC Current Gain : $h_{FE}=2000$ (Min.) ($V_{CE}=3V$, $I_C=3A$)
- Low Saturation Voltage : $V_{CE(sat)}=1.5V$ (Max.) ($I_C=3A$)
- Complementary to 2SB1641

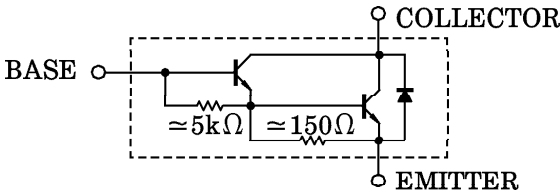
MAXIMUM RATINGS (Ta = 25°C)

CHARACTERISTIC		SYMBOL	RATING	UNIT
Collector-Base Voltage		V_{CBO}	100	V
Collector-Emitter Voltage		V_{CEO}	100	V
Emitter-Base Voltage		V_{EBO}	7	V
Collector Current	DC	I_C	5	A
	Pulse		8	
Base Current		I_B	0.5	A
Collector Power Dissipation		P_C	1.8	W
Junction Temperature		T_j	150	°C
Storage Temperature Range		T_{stg}	-55~150	°C



Weight : 1.5g

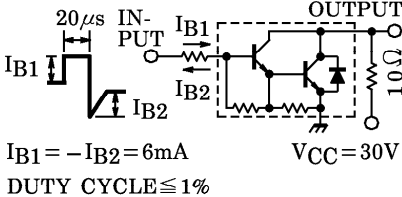
EQUIVALENT CIRCUIT



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ELECTRICAL CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC		SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current		ICBO	V _{CB} = 100V, I _E = 0	—	—	100	μA
Emitter Cut-off Current		IEBO	V _{EB} = 6V, I _C = 0	—	—	2.5	mA
Collector-Emitter Breakdown Voltage		V _(BR) CEO	I _C = 30mA, I _B = 0	100	—	—	V
DC Current Gain		h _{FE} (1)	V _{CE} = 3V, I _C = 3A	2000	—	15000	
		h _{FE} (2)	V _{CE} = 3V, I _C = 5A	1000	—	—	
Collector-Emitter Saturation Voltage		V _{CE} (sat) (1)	I _C = 3A, I _B = 6mA	—	1.1	1.5	V
		V _{CE} (sat) (2)	I _C = 5A, I _B = 20mA	—	1.3	2.5	
Base-Emitter Saturation Voltage		V _{BE} (sat)	I _C = 3A, I _B = 6mA	—	1.7	2.5	V
Switching Time	Turn-on Time	t _{on}	 I _{B1} = -I _{B2} = 6mA DUTY CYCLE ≤ 1%	—	1.0	—	μs
	Storage Time	t _{stg}		—	4.0	—	
	Fall Time	t _f		—	2.5	—	

